

Plastic Package

PNP SILICON PLANAR DARLINGTON POWER TRANSISTOR

BDW47

TO-220

B^CC C

General Purpose and Low Speed Switching Application

Complementary BDW42

ABSOLUTE MAXIMUM RATINGS

DESCRIPTION	SYMBOL	VALUE	UNIT	
Collector-Emitter Voltage	V _{CEO}	100	V	
Collector-Base Voltage	V _{CBO}	100	V	
Emitter-Base Voltage	V _{EBO}	5.0	V	
Collector Current Continuous	I _C	15	А	
Base Current	Ι _Β	0.5	А	
Total Device Dissipation @ T _c =25ºC Derate above 25ºC	PD	85 0.68	W W/ºC	
Operating And Storage Junction Temperature Range	T _{j,} T _{stg}	- 55 to +150	°C	

THERMAL RESISTANCE

Junction to CaseR1.47°C/W

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	MAX	UNIT
Collector Emitter Sustaining Voltage	$^{*}V_{\text{CEO}(\text{sus})}$	I _C =30mA, I _B =0	100		V
Collector Cutoff Current	I _{CEO}	V_{CE} =50V, I_{B} =0		2.0	mA
Collector Cutoff Current	I _{CBO}	V _{CB} =100V, I _E =0		1.0	mA
Emitter Cutoff Current	I _{EBO}	V_{BE} =5.0V, I _C =0		2.0	mA
DC Current Gain	*h _{FE}	I _C =5.0A, V _{CE} =4.0V	1000		
		I _C =10A, V _{CE} =4.0V	250		
Collector Emitter Saturation Voltage	*V _{CE (sat)}	I _C =5.0A, I _B =10mA		2.0	V
		I _C =10A, I _B =50mA		3.0	V
Base Emitter On Voltage	*V _{BE (on)}	I _C =10A, V _{CE} =4.0V		3.0	V

SECOND BREAKDOWN

Second Breakdown Collector Current	**	$V_{CE} = 22.5V$	3.8	А
with Base Forward Biased		V _{CE} = 36V	1.2	A

DYNAMIC CHARACTERISTICS

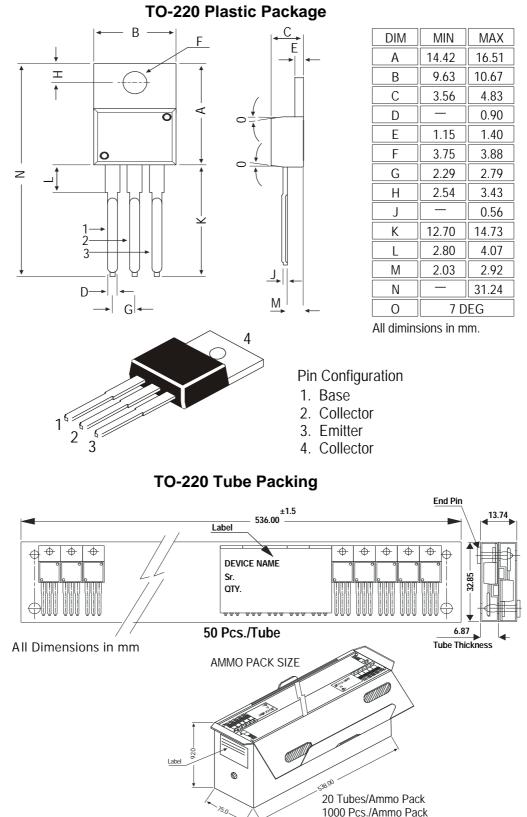
Transition Frequency	f _T	I_{C} =3.0A, V_{CE} =3.0V, f=1MHz	4.0		MHz
Output Capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=0.1MHz		300	рF
Small-Signal Current Gain	h _{fe}	I _C =3.0A, V _{CE} =3.0V, f=1kHz	300		

* Pulse test : Pulse Width =300ms, Duty Cycle = 2.0%

** Pulse test non repetitive : Pulse Width = 250 ms

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Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-220	200 pcs/polybag 50 pcs/tube	396 gm/200 pcs 120 gm/50 pcs	3" x 7.5" x 7.5" 3.5" x 3.7" x 21.5"	1.0K 1.0K	17" x 15" x 13.5" 19" x 19" x 19"	16.0K 10.0K	36 kgs 29 kgs

BDW47Rev140803E

Continental Device India Limited

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Disclaimer

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